

# BLW76

## NPN SILICON RF POWER TRANSISTOR

### DESCRIPTION:

**BLW76** is Designed for use in class-AB or class-B operated high power transmitters in the H.F. and V.H.F bands and, as a Linear amplifier in the H.F. band.

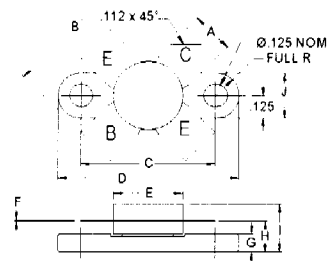
### FEATURES:

- $P_G = 18$  dB min. at 75 W/30 MHz
- $IMD_3 = -30$  dBc max. at 75 W (PEP)
- **Omnigold™** Metalization System

### MAXIMUM RATINGS

$I_C$	10 A
$V_{CB}$	60 V
$V_{CE}$	35 V
$P_{DISS}$	140 W @ $T_C = 25^\circ C$
$T_J$	$-65^\circ C$ to $+200^\circ C$
$T_{STG}$	$-65^\circ C$ to $+150^\circ C$
$\theta_{JC}$	1.05 $^\circ C/W$

### PACKAGE STYLE .380 4L FLG



DIM	MINIMUM <small>(inches / mm)</small>	MAXIMUM <small>(inches / mm)</small>
A	.220 / 5.59	.230 / 5.84
B	.785 / 19.94	
C	.720 / 18.29	.730 / 18.54
D	.970 / 24.64	.980 / 24.89
E		.385 / 9.78
F	.004 / 0.10	.006 / 0.15
G	.085 / 2.16	.105 / 2.67
H	.160 / 4.06	.180 / 4.57
I		.280 / 7.11
J	.240 / 6.10	.255 / 6.48

### CHARACTERISTICS $T_C = 25^\circ C$

SYMBOL	TEST CONDITIONS			MINIMUM	TYPICAL	MAXIMUM	UNITS
$BV_{CEO}$	$I_C = 50$ mA			35			V
$BV_{CER}$	$I_C = 50$ mA	$R_{BE} = 10 \Omega$		60			V
$BV_{EBO}$	$I_E = 10$ mA			4.0			V
$I_{CES}$	$V_E = 28$ V					5.0	mA
$h_{FE}$	$V_{CE} = 5.0$ V	$I_C = 1.0$ A		10		100	---
$C_{ob}$	$V_{CB} = 28$ V		$f = 1.0$ MHz			80	pF
$G_{PE}$	$V_{CE} = 25$ V	$I_{CQ} = 3.2$ A	$f = 225$ MHz	13.5	14.5		dB
$IMD_3$	$P_{REF} = 16$ W	Vision = -8 dB Side Band = -16 dB	Snd. = -7 dB			-55	dBc

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